NSN 5961-01-483-2610

No Fiig: A110a0

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-483-2610 **Inclosure Material:** Plastic **Overall Length:** Between 5.890 millimeters and 6.860 millimeters **End Application:** Rvr new generation **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 collector to emitter voltage, dc and 30.0 collector to base voltage, dc and 5.0 emitter to base voltage, dc and 5.0 emitter to collector voltage, dc **Special Features:** Phototransistor **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:**